



# STPS40L40CT/CW

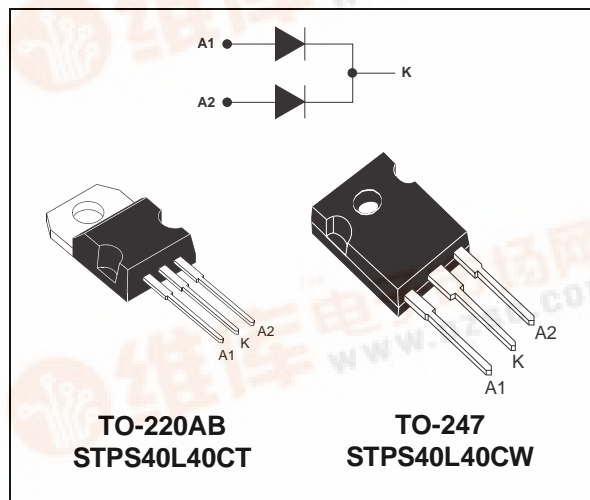
## LOW DROP POWER SCHOTTKY RECTIFIER

### MAIN PRODUCTS CHARACTERISTICS

<b>I<sub>F(AV)</sub></b>	<b>2 x 20 A</b>
<b>V<sub>RRM</sub></b>	<b>40 V</b>
<b>T<sub>j (max)</sub></b>	<b>150 °C</b>
<b>V<sub>F (max)</sub></b>	<b>0.49 V</b>

### FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP MEANING VERY SMALL CONDUCTION LOSSES
- LOW DYNAMIC LOSSES AS A RESULT OF THE SCHOTTKY BARRIER
- AVALANCHE RATED



### DESCRIPTION

Dual center tap Schottky barrier rectifier designed for high frequency Switched Mode Power Supplies and DC to DC converters.

Packaged in TO-220AB and TO-247 this device is intended for use in low voltage, high frequency inverters, free-wheeling and polarity protection applications.

### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage		40	V
I <sub>F(RMS)</sub>	RMS forward current		30	A
I <sub>F(AV)</sub>	Average forward current	T <sub>c</sub> = 130°C	20	A
		δ = 0.5	40	
I <sub>FSM</sub>	Surge non repetitive forward current	tp = 10 ms Sinusoidal	230	A
I <sub>R(RM)</sub>	Repetitive peak reverse current	tp = 2 μs square F = 1kHz	2	A
I <sub>R(SM)</sub>	Non repetitive peak reverse current	tp = 100 μs square	3	A
T <sub>stg</sub>	Storage temperature range		- 65 to + 150	°C
T <sub>j</sub>	Maximum operating junction temperature *		150	°C
dV/dt	Critical rate of rise of reverse voltage		10000	V/μs

\* :  $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink



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### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.5	$^{\circ}\text{C}/\text{W}$
		Total	0.8	
$R_{th(c)}$		Coupling	0.1	$^{\circ}\text{C}/\text{W}$

When the diodes 1 and 2 are used simultaneously :  
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

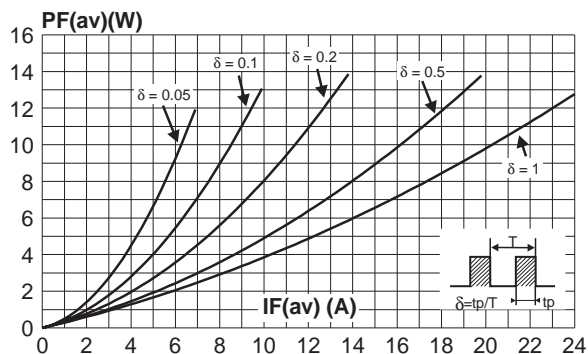
### STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			0.8	mA
		$T_j = 100^{\circ}\text{C}$			30	70	mA
$V_F^*$	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 20\text{ A}$			0.53	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 20\text{ A}$		0.42	0.49	
		$T_j = 25^{\circ}\text{C}$	$I_F = 40\text{ A}$			0.69	
		$T_j = 125^{\circ}\text{C}$	$I_F = 40\text{ A}$		0.6	0.7	

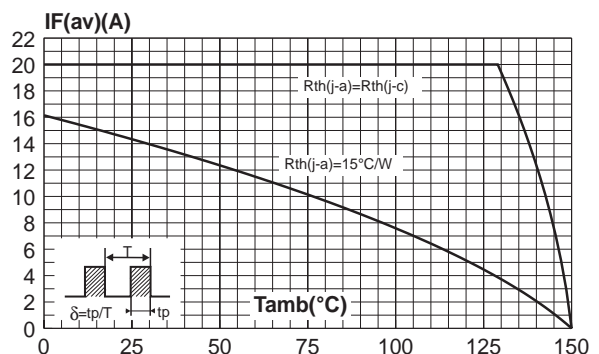
Pulse test : \*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation :  
 $P = 0.28 \times I_{F(AV)} + 0.0105 I_{F(RMS)}^2$

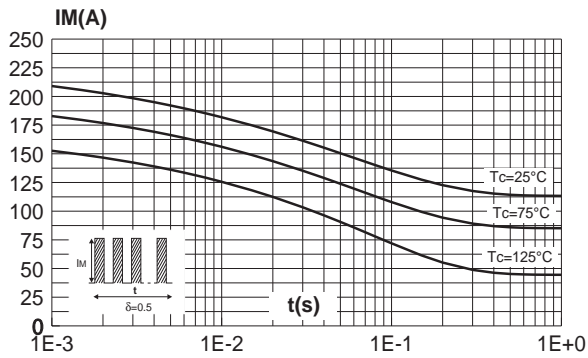
**Fig. 1:** Average forward power dissipation versus average forward current (per diode).



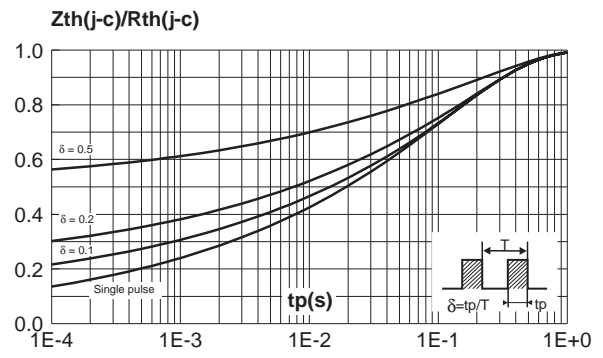
**Fig. 2:** Average current versus ambient temperature ( $\delta = 0.5$ , per diode).



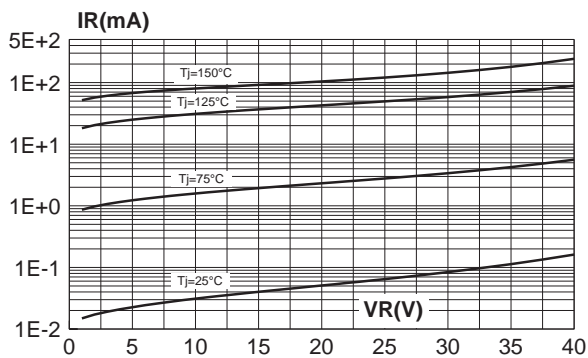
**Fig. 3:** Non repetitive surge peak forward current versus overload duration (maximum values, per diode).



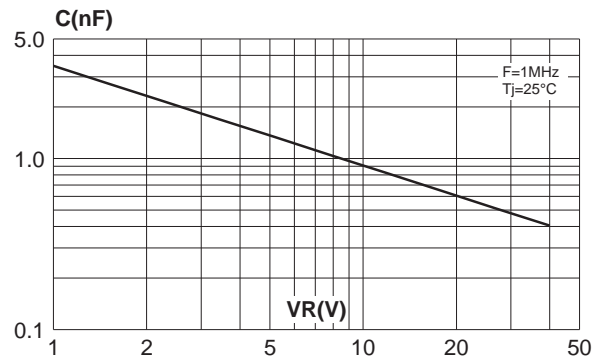
**Fig. 4:** Relative variation of thermal impedance junction to case versus pulse duration.



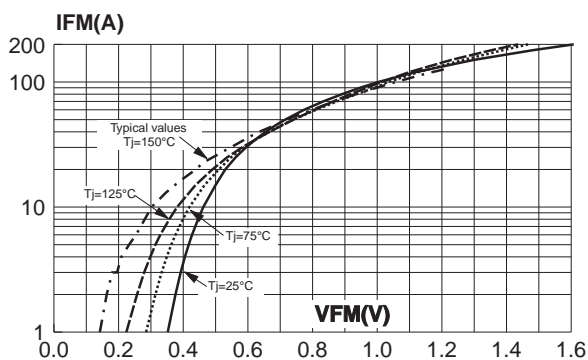
**Fig. 5:** Reverse leakage current versus reverse voltage applied (typical values, per diode).



**Fig. 6:** Junction capacitance versus reverse voltage applied (typical values, per diode).

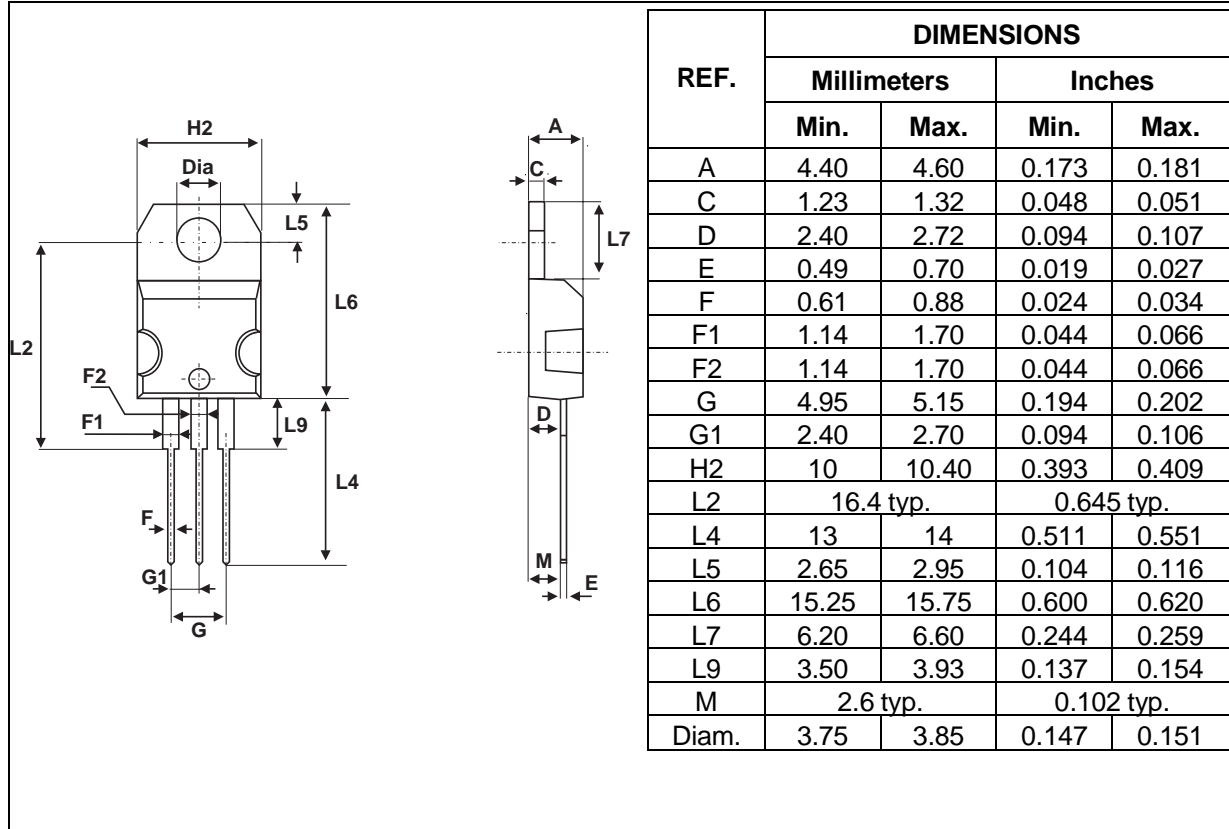


**Fig. 7:** Forward voltage drop versus forward current (maximum values, per diode).



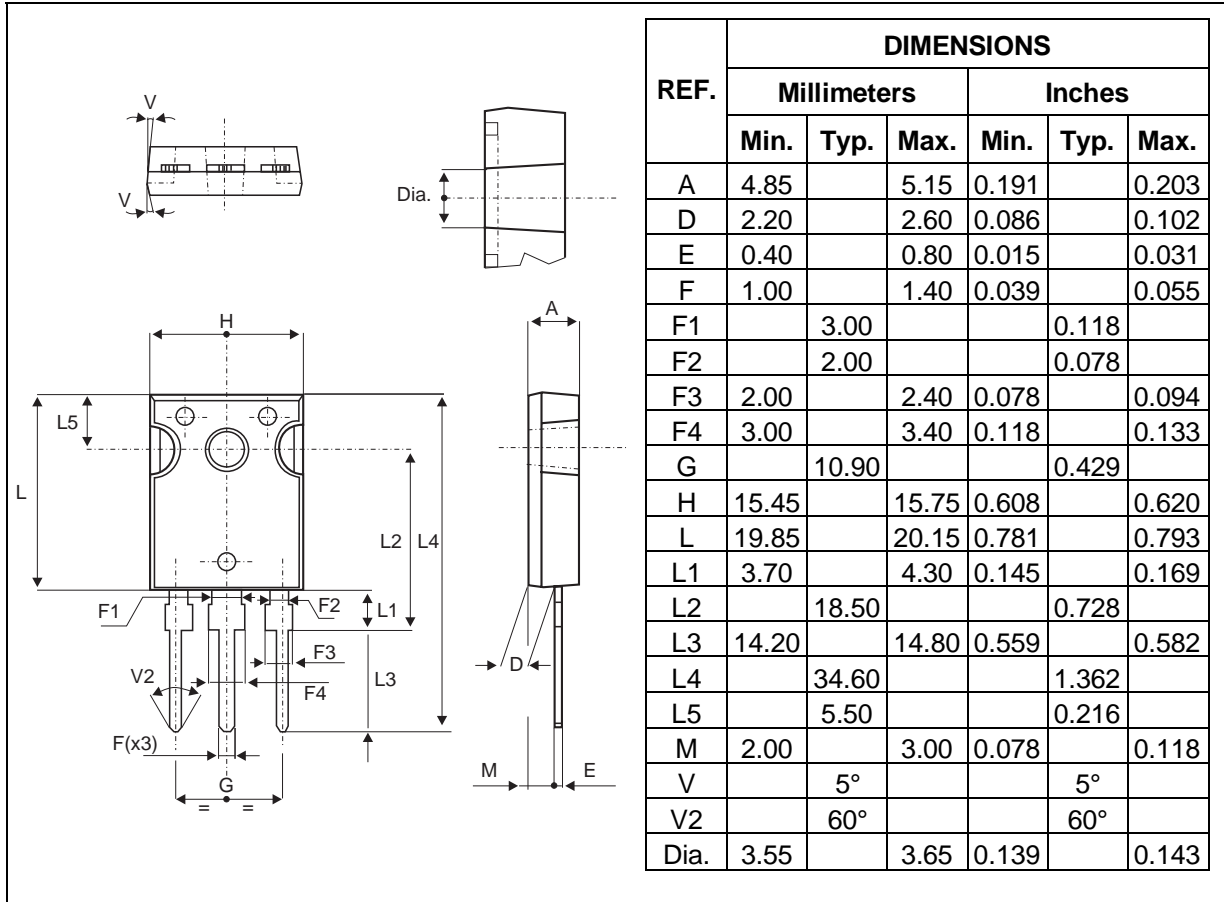
## STPS40L40CT/CW

### PACKAGE MECHANICAL DATA TO-220AB



- Cooling method : C
- Recommended torque value : 0.55m.N
- Maximum torque value : 0.70 m.N

**PACKAGE MECHANICAL DATA**  
TO-247



- Cooling method : C
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS40L40CT	STPS40L40CT	TO-220AB	2g	50	Tube
STPS40L40CW	STPS40L40CW	TO-247	4.4g	30	Tube

- Epoxy meets UL94,V0

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